

A cross-sectional view of a semiconductor device. It features a substrate 1204 with a central channel region. Three gates, labeled 1213, are positioned on top of the channel region. Each gate 1213 is flanked by side gates, labeled 1214, which are positioned on the sides of the channel region. The side gates 1214 are connected to the gates 1213. The substrate 1204 is shown with a hatched pattern.

A cross-sectional view of a semiconductor device 1200. The device features a substrate 1202 with a patterned layer 1203 on its top surface. A central region contains three rectangular openings. Above these openings, there are three rectangular blocks, each with a cross-hatched pattern. On the top surface of the substrate 1202, there are two circular features, each with a diagonal hatching pattern, labeled 1216. A thin, uniform layer 1215 covers the top surface of the entire device, including the circular features 1216.

FIG. 10E

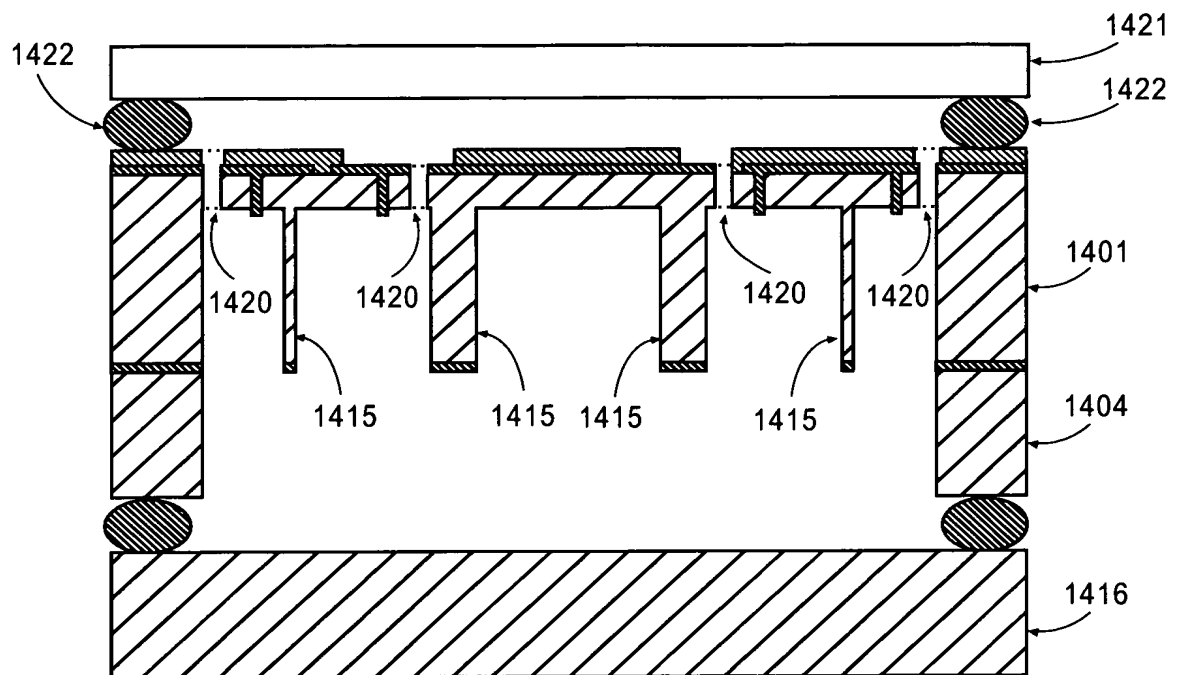


FIG. 12E